





# ZXTP749F

#### PNP LOW V<sub>CE(sat)</sub> TRANSISTOR IN SOT-23

#### Features

- BV<sub>CEO</sub> > -25V •
- $BV_{CBO} > -35V$ •
- I<sub>C(cont)</sub> = -3A Continuous Currrent •
- V<sub>CE(sat)</sub> < -150mV @ -1A •
- $R_{CE(sat)} = 87 \text{ m}\Omega$ •
- $P_{D} = 0.725W$ •
- -6A Peak Pulse Current •
- -25V Forward Blocking Voltage
- Complementary part number ZXTN649F
- Lead, Halogen and Antimony Free, RoHS Compliant • (Note 1)
- "Green" Device (Note 2)

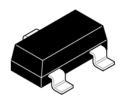
## **Applications**

- MOSFET gate drivers
- Power switches
- Motor control •

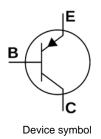
### **Mechanical Data**

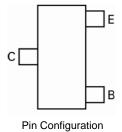
- Case: SOT-23
- Case Material: Molded Plastic. "Green" Molding Compound. •
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (approximate)

SOT-23



Top View





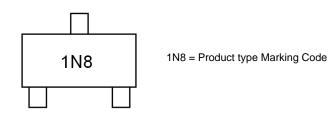
## **Ordering Information**

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP749FTA	1N8	7	8mm	3000

Notes:

No purposefully added lead. Halogen and Antimony Free.
Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

## **Marking Information**









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## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	35	V
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current (Note 4)	Ic	3	А
Peak Pulse Current	I <sub>CM</sub>	6	А
Base Current	I <sub>B</sub>	500	mA

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = 25^{\circ}C$ (Note 3)	PD	725	mW
Thermal Resistance, Junction to Ambient (Note 3) @ $T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	172	°C/W
Thermal Resistance, Junction to Lead @ T <sub>A</sub> = 25°C	$R_{ ext{ heta}JL}$	79	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

3. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions 4. For device mounted on FR4 PCB measured at t  $\leq$  2 Secs. Notes:

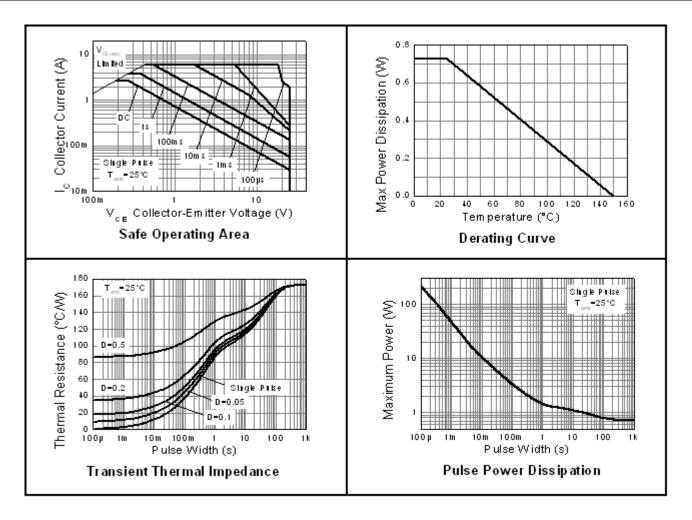






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# Thermal Characteristics and Derating information









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# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-35	60		V	I <sub>C</sub> = -100 μA
Collector-Emitter Breakdown Voltage (Note 5)	V <sub>(BR)CEO</sub>	-25	40		V	I <sub>C</sub> = -10 mA
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-7	8.4		V	I <sub>E</sub> = 100 μA
Collector Cutoff Current	I <sub>CBO</sub>		< 1	-50 -0.5	nΑ μΑ	$V_{CB} = -28V$ $V_{CB} = -28V$ , $T_{amb}=100^{\circ}C$
Emitter Cutoff Current	I <sub>EBO</sub>		< 1	-50	. nA	V <sub>EB</sub> = -5.6V
Static Forward Current Transfer Ratio (Note 5)	h <sub>FE</sub>	200 130 100 25	320 230 180 50	500		$\label{eq:lc} \begin{array}{l} I_{C} = -100 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_{C} = -1 \text{A}, \ V_{CE} = -2 \text{V} \\ I_{C} = -2 \text{A}, \ V_{CE} = -2 \text{V} \\ I_{C} = -6 \text{A}, \ V_{CE} = -2 \text{V} \end{array}$
Collector-Emitter Saturation Voltage (Note 5)	V <sub>CE(sat)</sub>		-85 -229	-150 -350	mV mV	I <sub>C</sub> =-1A, I <sub>B</sub> = -100mV I <sub>C</sub> = -3A, I <sub>B</sub> = -300mV
Base-Emitter Turn-On Voltage (Note 5)	V <sub>BE(on)</sub>		-786	-850	mV	$I_c = -1A, V_{CE} = -2V$
Base-Emitter Saturation Voltage (Note 5)	V <sub>BE(sat)</sub>		-895	-1000	mV	$I_c = -1A$ , $I_B = -100mV$

5. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu s.$  Duty cycle  $\leq$  2% Notes:



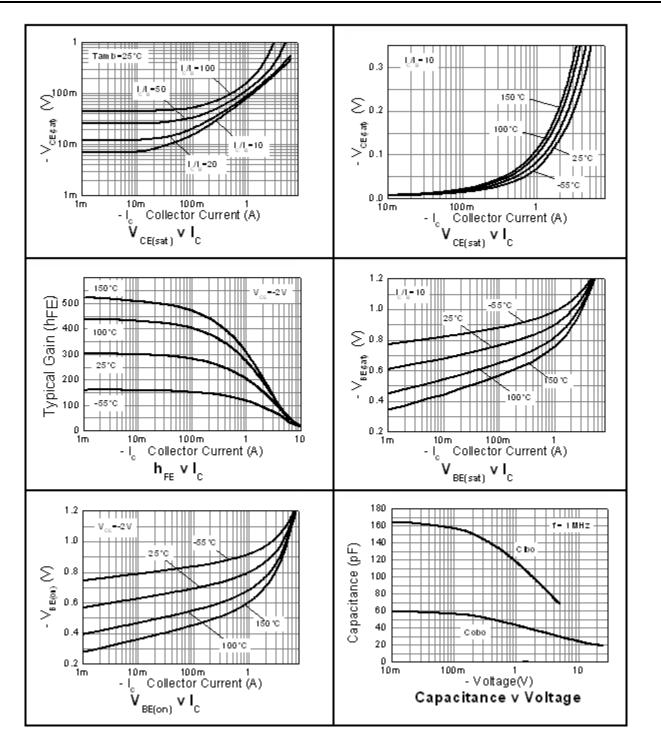
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# **Typical Characteristics**





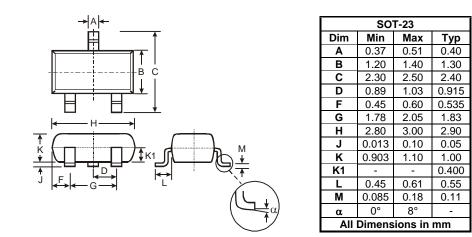
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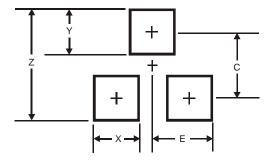


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# **Package Outline Dimensions**



## Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35





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